

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1425

POWER AMPLIFIER APPLICATIONS.

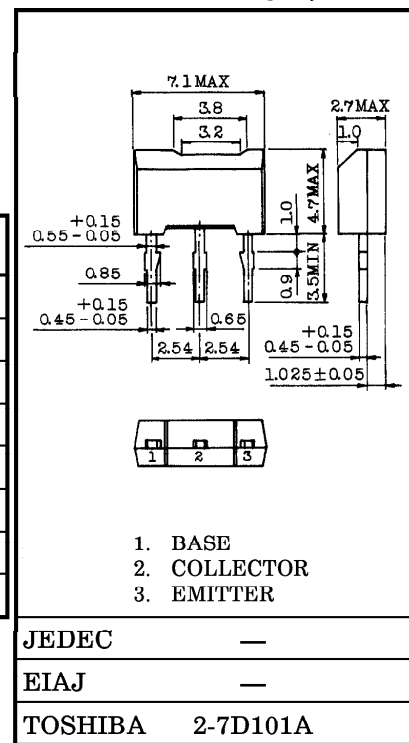
DRIVER STAGE AMPLIFIER APPLICATIONS.

Unit in mm

- Complementary to 2SC3665.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-120	V
Collector-Emitter Voltage	V _{CEO}	-120	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-800	mA
Base Current	I _B	-80	mA
Collector Power Dissipation	P _C	1000	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.2g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = -120V, I _E = 0	—	—	-100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _C = 0	—	—	-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = -10mA, I _B = 0	-120	—	—	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = -1mA, I _C = 0	-5	—	—	V
DC Current Gain	h _{FE} (Note)	V _{CE} = -5V, I _C = -100mA	80	—	240	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -500mA, I _B = -50mA	—	—	-1.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -5V, I _C = -500mA	—	—	-1.0	V
Transition Frequency	f _T	V _{CE} = -5V, I _C = -100mA	—	120	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	—	40	pF

Note : h_{FE} Classification O : 80~160, Y : 120~240

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